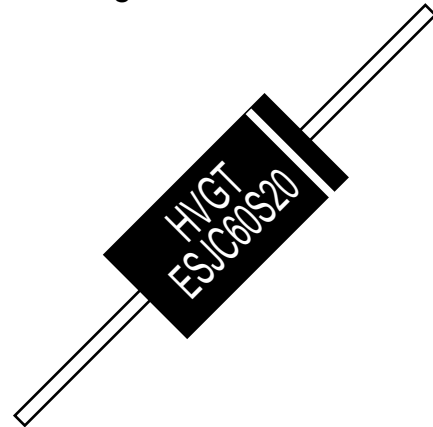




High reliability resin molded type high voltage diode in small size package which is sealed a multilayered mesa type silicon chip by epoxy resin.

Outline Drawings :



Features

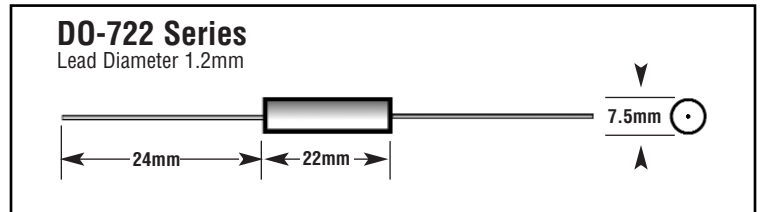
- High speed switching
- Epoxy resin molded in vacuum, Have anticorrosion in the surface
- High surge resistivity for CRT discharge
- High reliability design
- Avalanche characteristic

Applications

- X light Power supply
- Laser
- Voltage doubler circuit
- Microwave emission power
- General purpose high voltage rectifier, Voltage multiplier assembly.

Maximum Ratings and Characteristics

- Absolute Maximum Ratings



Items	Symbols	Condition	ESJC60S20	Units
Repetitive Peak Reverse Voltage	V_{RRM}	$T_a=25^{\circ}C, I_R=0.1mA$	20	kV
Average Output Current	I_o	$T_a=25^{\circ}C, Resistive Load$	0.4	A _{peak}
Surge Current	I_{FSM}	$T_a=25^{\circ}C, 8.3msec, half sine$	30	A _{peak}
Junction Temperature	T_j		125	$^{\circ}C$
Allowable Operation Case Temperature	T_c		125	$^{\circ}C$
Storage Temperature	T_{stg}		-40 to +125	$^{\circ}C$

- Electrical Characteristics ($T_a=25^{\circ}C$ Unless otherwise specified)

Items	Symbols	Conditions	ESJC60S20	Units
Maximum Forward Voltage Drop	V_F	at $25^{\circ}C, at: I_F$	18	V
Maximum Reverse Current	IR1	at $25^{\circ}C, V_R=V_{RRM}$	5.0	μA
	IR2	at $100^{\circ}C, V_R=V_{RRM}$	50	μA
Maximum Reverse Recovery Time	T_{rr}	at $25^{\circ}C; I_F=0.5I_R; I_R=I_F(AV); I_{rr}=0.25I_R$	--	nS
Junction Capacitance	C_j	at $25^{\circ}C; V_R=0V, f=1MHz$	--	pF